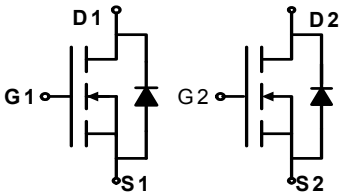
AP6H03S

30V N+N-Channel Enhancement Mode MOSFET

Description

The AP6H03Suses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge . The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications



General Features

N-Channel

V_{DS} = 30V,I_D =7.5A
$R_{DS(ON)}$ < 16mΩ@ V_{GS}=10V

NChannel

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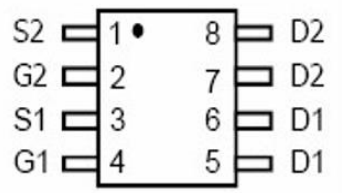
High power and current handing capability

Lead free product is acquired

Surface mount package

Schematic diagram



Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP6H03S	SOP-8	AP6H03S YYWWWW	3000

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25°C)	7.5	A
	Drain Current – Continuous (T_C=100°C)	4.8	A
I_{DM}	Drain Current – Pulsed[1]	30	A
EAS	Single Pulse Avalanche Energy[2]	14	mJ
IAS	Single Pulse Avalanched Current[2]	17	A
P_D	Power Dissipation (T_C=25°C)	2.1	W
	Power Dissipation – Derate above 25°C	0.017	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	60	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted) Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃, I_D=1mA	---	0.04	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
$R_{DS(ON)}$	Static Drain-Source On-Resistance[3]	V_{GS}=10V , I_D=6A	---	15	20	mΩ
		V_{GS}=4.5V , I_D=3A	---	23	30	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.5	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	mV/℃
gfs	Forward Transconductance	V_{DS}=10V , I_D=6A	---	13	---	S
Q_g	Total Gate Charge[3,4]	V_{DS}=15V , V_{GS}=4.5V , I_D=5A	---	4.1	8	nC
Q_{gs}	Gate-Source Charge[3,4]		---	1	2	
Q_{gd}	Gate-Drain Charge[3,4]		---	2.1	4	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=15V , V_{GS}=10V , R_G=6 I_D=1A	---	2.6	5	ns
T_r	Rise Time[3,4]		---	7.2	14	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	15.8	30	
T_f	Fall Time[3,4]		---	4.6	9	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	345	500	pF
C_{oss}	Output Capacitance		---	55	80	
C_{rss}	Reverse Transfer Capacitance		---	32	55	
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	---	3.2	6.4	Ω
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	7.5	A
I_{SM}	Pulsed Source Current[3]		---	---	30	A
V_{SD}	Diode Forward Voltage[3]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	V_{GS}=0V,I_S=1A , di/dt=100A/μs T_J=25℃	---	---	---	ns
Q_{rr}	Reverse Recovery Charge		---	---	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. VThe data tested by pulsed , pulse width DD=25V,VGS=10V,L=0.1mH,IAS=17A.,RG≦=25 300us , duty cycle ,Starting TJ=25≦℃. 2%.
3. Essentially independent of operating temperature.

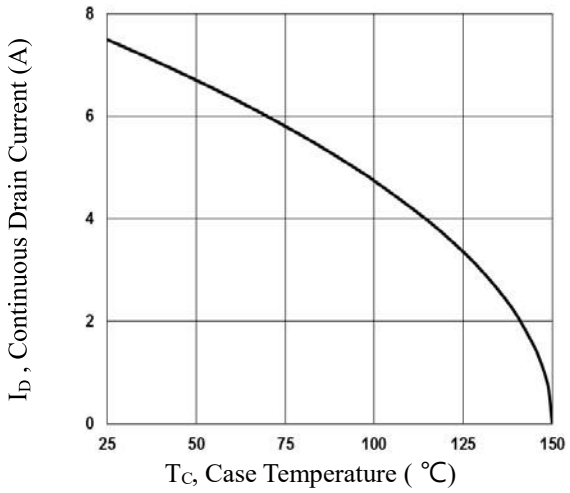


Fig.1 Continuous Drain Current vs. T_C

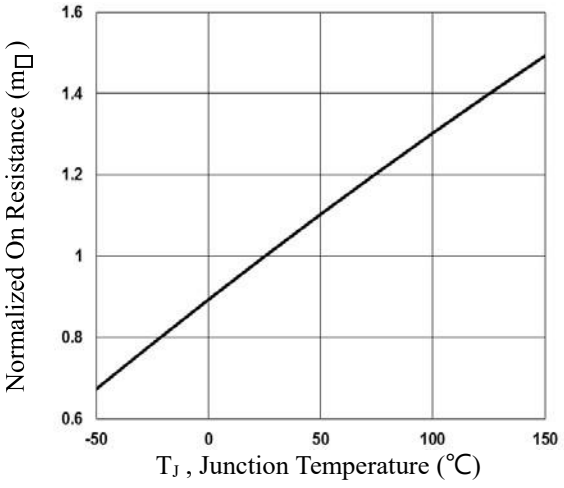


Fig.2 Normalized RDSON vs. T_J

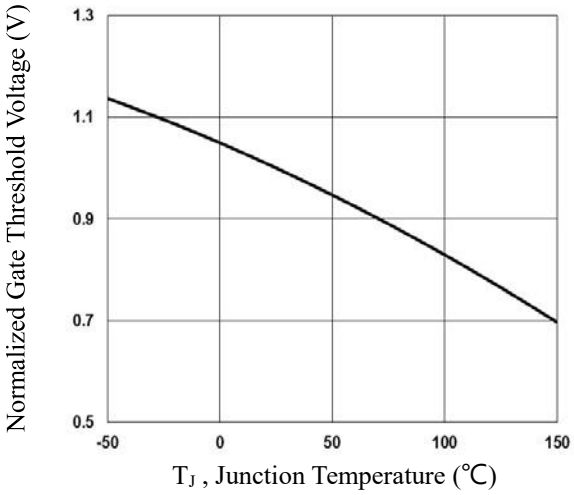


Fig.3 Normalized V_{th} vs. T_J

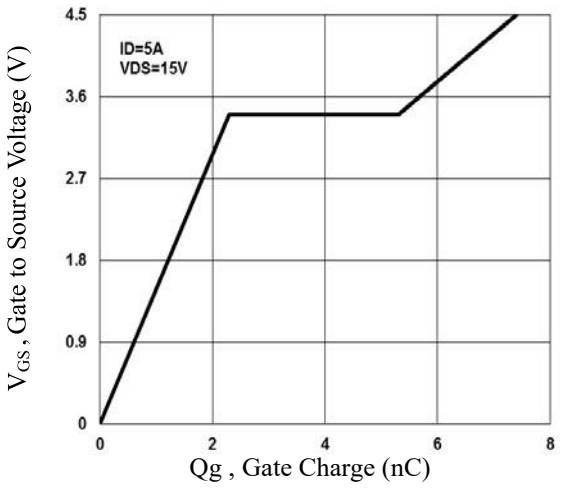


Fig.4 Gate Charge Waveform

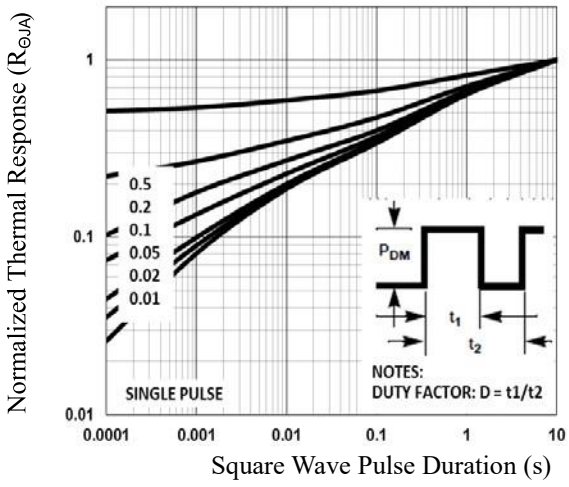


Fig.5 Normalized Transient Response

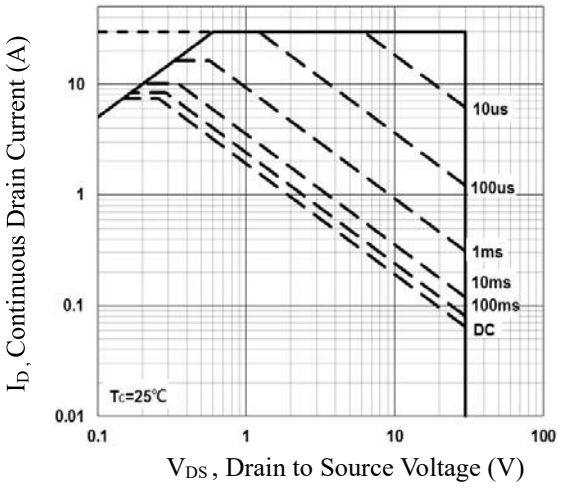


Fig.6 Maximum Safe Operation Area

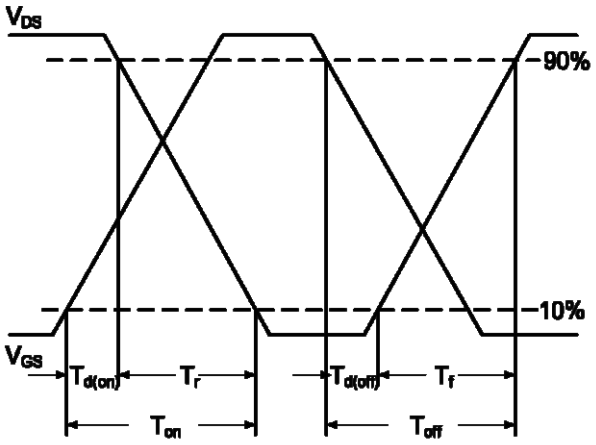


Fig.7 Switching Time Waveform

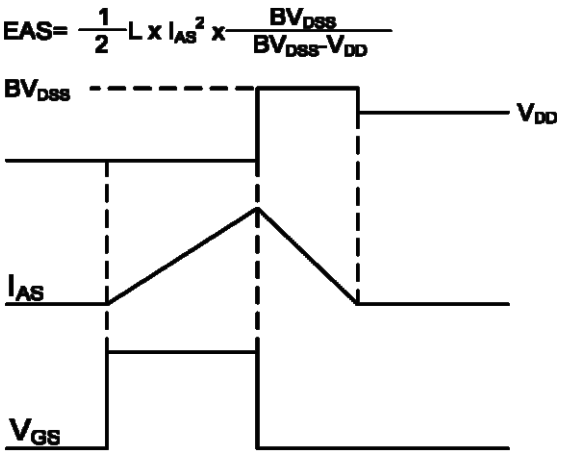


Fig.8 EAS waveform

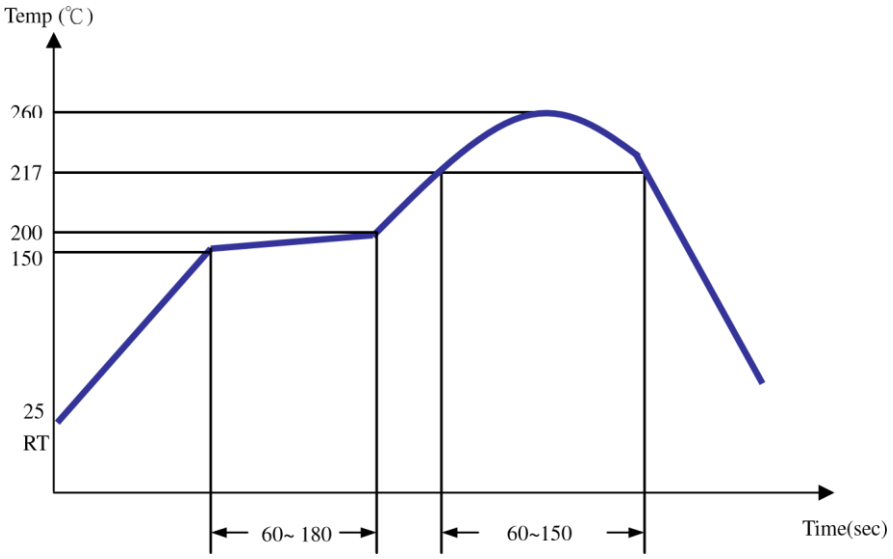
Reflow Soldering

The choice of heating method may be influenced by plastic QFP package). If infrared or vapor phase heating is used and the package is not absolutely dry (less than 0.1% moisture content by weight), vaporization of the small amount of moisture in them can cause cracking of the plastic body. Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stenciling or pressure-syringe dispensing before package placement. Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 270 °C depending on solder paste material. The top-surface temperature of the packages should preferable be kept below 245 °C for thick/large packages (packages with a thickness 2.5 mm or with a volume 350 mm^3 so called thick/large packages). The top-surface temperature of the packages should preferable be kept below 260 °C for thin/small packages (packages with a thickness < 2.5 mm and a volume < 350 mm^3 so called thin/small packages).

Stage	Condition	Duration
1'st Ram Up Rate	max3.0+/-2 /sec	-
Preheat	150 ~200	60~180 sec
2'nd Ram Up	max3.0+/-2 /sec	-
Solder Joint	217 above	60~150 sec
Peak Temp	260 +0/-5	20~40 sec
Ram Down rate	6 /sec max	-



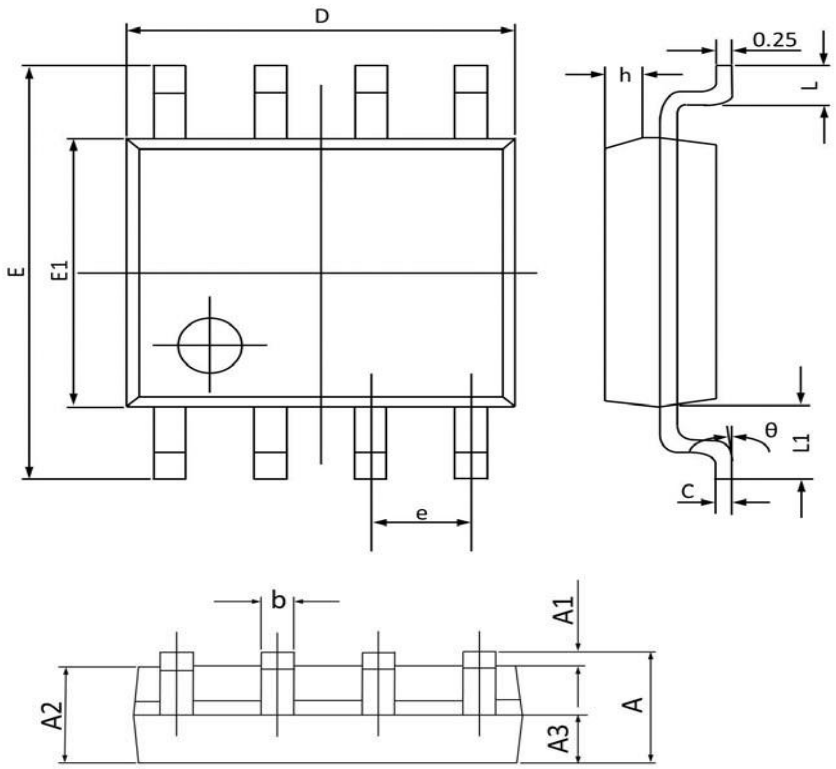
Wave Soldering:

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

Manual Soldering:

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

SOP8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050(BSC)		0.041(BSC)	
θ	0°	8°	0°	8°

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